



High-end Power Semiconductor Manufacturer

Fast Switching Thyristor**Features**

- High current rating
- Excellent dynamic characteristics
- Superior surge capabilities
- Standard package
- Metric Device version available

Typical Applications

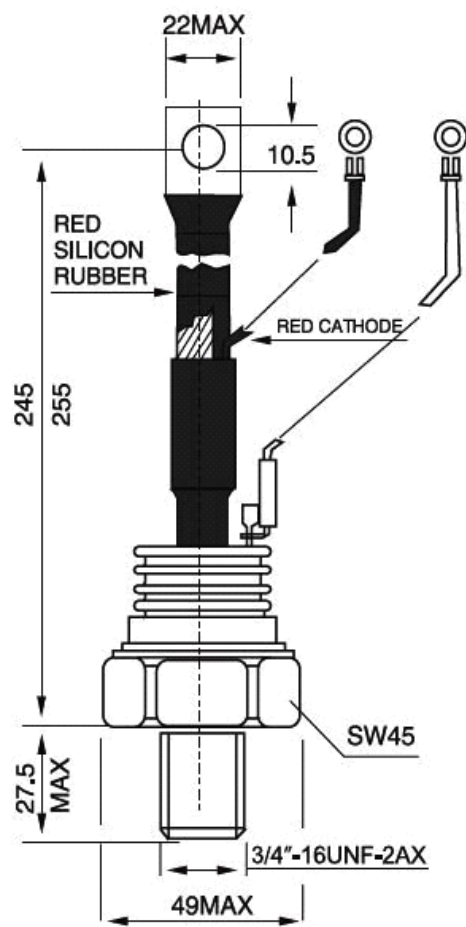
- Phase control applications in converters
- Lighting circuits
- Battery charges
- Regulated power supplies and temperature and speed control circuit
- Can be supplied to meet stringent military, aerospace and other high-reliability requirement
- Power supplier & motor controls

**ELECTRICAL CHARACTERISTICS**

Symbol	Parameter	Conditions	KKS300		KKS350	Unit
$I_{T(AV)}$	Average on-state current	$T_c=55^\circ\text{C}$	300		350	A
$I_{T(RMS)}$	RMS on-state current	$T_c=55^\circ\text{C}$	480		560	A
I_{TSM}	Surge on current	$T_c=25^\circ\text{C}$ 10ms	11000		125000	A
I^2t	I^2t value	$T_c=25^\circ\text{C}$ 10ms	600000		710000	A
V_{RRM}	Repetitive peak reverse voltage	$T_c=140^\circ\text{C}$	400-2600			V
I_{RRM}	Repetitive peak reverse current	$T_c=140^\circ\text{C}$	≤ 35.0		≤ 40.0	mA
V_{TM}	On-state voltage	$T_c=25^\circ\text{C}$	2.15		2.2	V
I_{TM}	On-state Current	$T_c=25^\circ\text{C}$	900		1050	A
I_{GT}	Gate Trigger Current	$T_c=25^\circ\text{C}$	50-200			mA
V_{GT}	Gate Trigger Voltage	$T_c=25^\circ\text{C}$	≤ 2.5			V
V_{GD}	Max DC gate voltage not to trigger	$T_j=125^\circ\text{C}$, DC	0.28			V
I_H	Holding Current	$T_c=25^\circ\text{C}$	≤ 600			mA
t_q	turn-off time	$T_c=25^\circ\text{C}$	20-30			us
dv/dt	Rate Of Rise Of On-State Voltage	$T_c=25^\circ\text{C}$	≥ 800			V/us
di/dt	Rate Of Rise Of On-State Current	$T_c=25^\circ\text{C}$	≥ 100			A/us
R_{j-c}	Peak gate forward voltage		≤ 0.1		≤ 0.07	$^\circ\text{C}/\text{W}$
T_j	Junction temperature		$-40\sim+125$			$^\circ\text{C}$
T_{stg}	Storage temperature		$-40\sim+125$			$^\circ\text{C}$
MT	Mounting torque		≤ 305.0			N·m
Wt	Weight	Typical value	580		600	g

Outline table

(Dimension in mm)



*FOR METRIC DEVICES;
M20×1.5/M24×1.5-LENGTH 21 MAX

T5

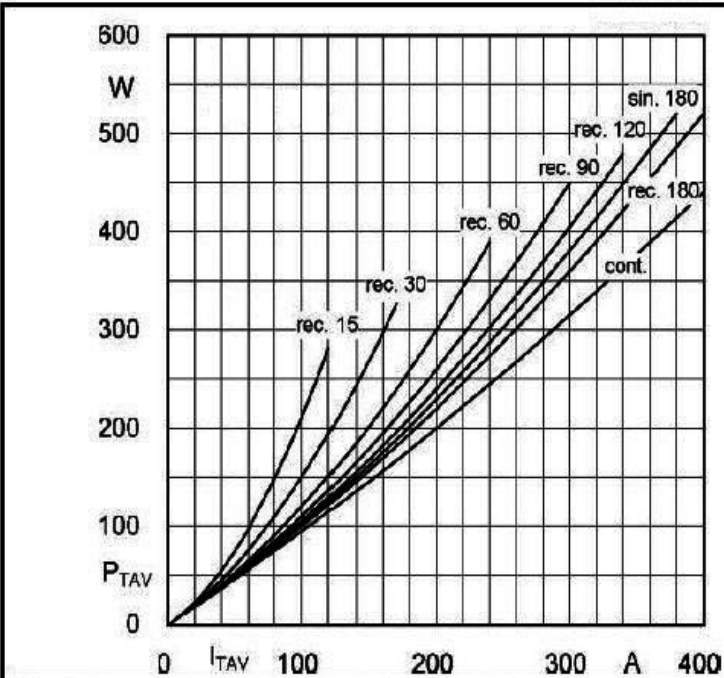


Fig. 1L Power dissipation vs. on-state current

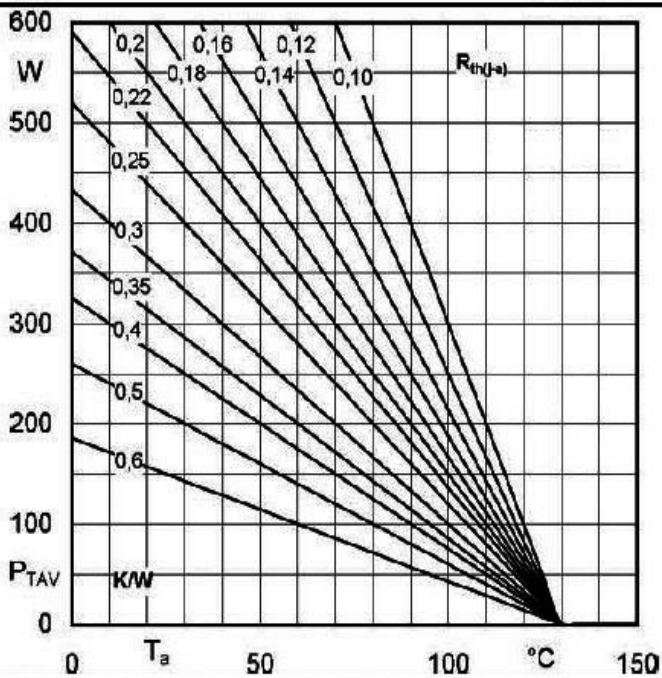


Fig. 1R Power dissipation vs. ambient temperature

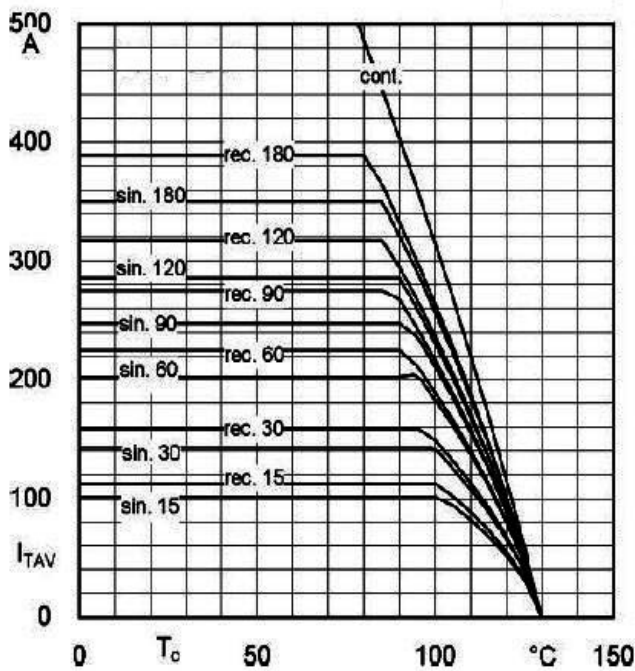


Fig. 2 Rated on-state current vs. case temperature

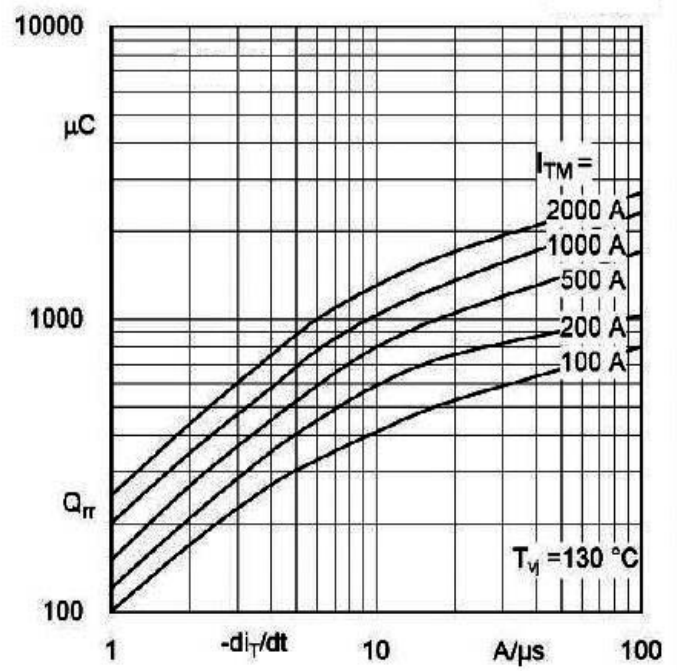


Fig. 3 Recovered charge vs. current decrease

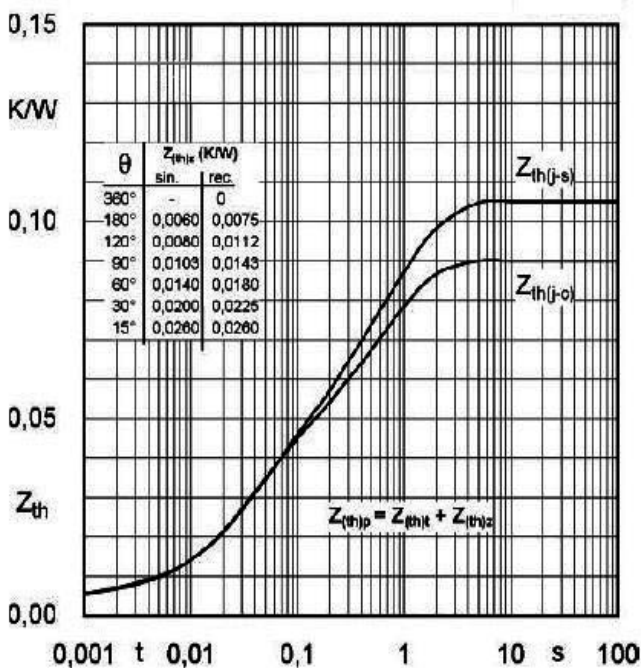


Fig. 4 Transient thermal impedance vs. time

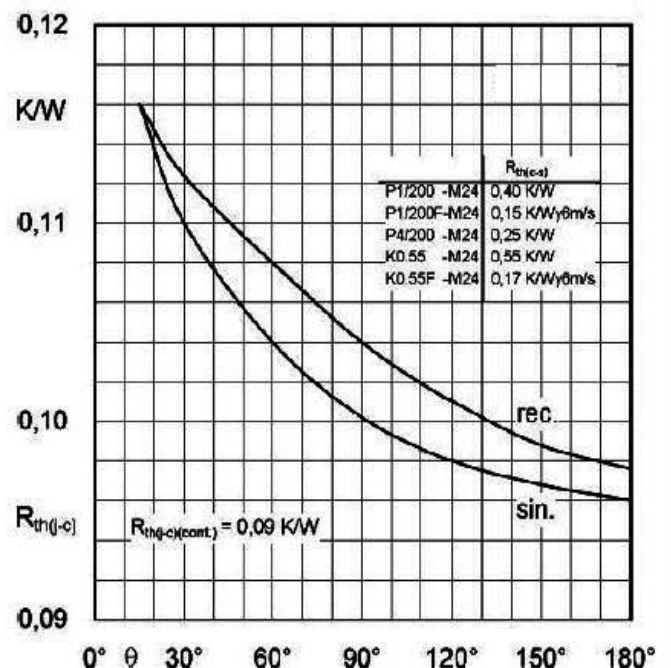


Fig. 5 Thermal resistance vs. conduction angle

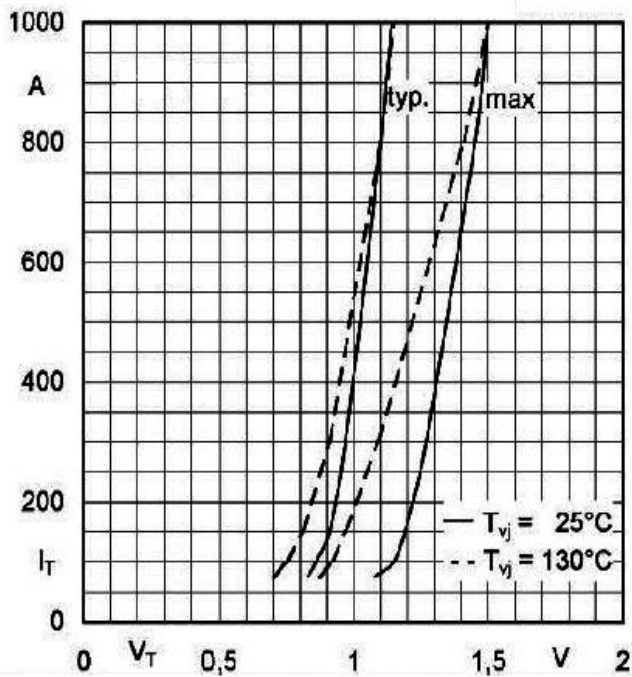


Fig. 6 On-state characteristics

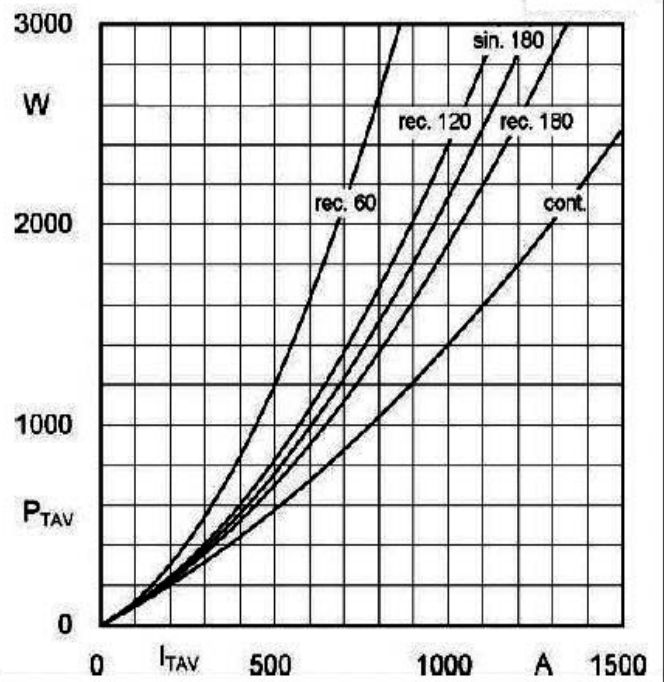


Fig. 7 Power dissipation vs. on-state current

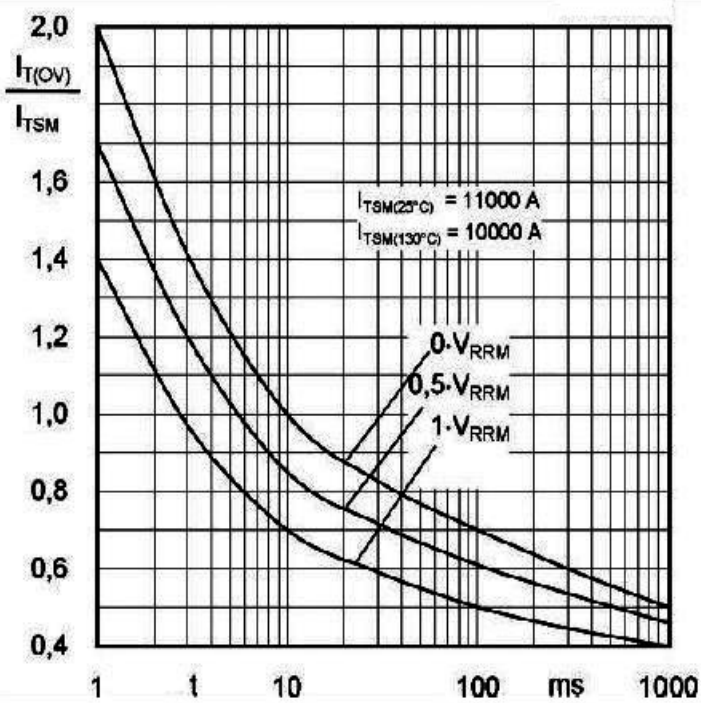


Fig. 8 Surge overload current vs. time